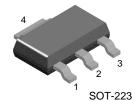


# **NZT6727**

# **PNP General Purpose Amplifier**

- This device is designed for general purpose medium power amplifiers and switches requiring collecor currents to 1.0A.
- Sourced from process 77.



1. Base 2. Collector 3. Emitter

# **Absolute Maximum Ratings\*** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	-40	V
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5.0	V
I <sub>C</sub>	Collector Current - Continuous	-1.5	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above whitch the serviceability of any semiconductor device may be impaird.

- NOTES:
  1. These ratings are based on a maximum junction temperature of 150 degrees C.
  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Off Characte	Off Characteristics					
V <sub>(BR)CEO</sub>	Collector-Emitter Sustaining Voltage *	$I_C = -10 \text{mA}, I_B = 0$	-40		V	
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -1.0 \text{mA}, I_E = 0$	-50		V	
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5.0		V	
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = -50V, I_{E} = 0$		-0.1	μΑ	
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5.0V, I_C = 0$		-0.1	μΑ	
On Characteristics						
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1.0V	55			
		$I_C = -100 \text{mA}, V_{CE} = -1.0$	60			
		$I_C = -1.0A, V_{CE} = -1.0V$	50	250		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1.0A, I <sub>B</sub> = -100mA		-0.5	V	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$I_C = -1.0A, V_{CE} = -1.0V$		-1.2	V	
Small Signal Characteristics						
h <sub>fe</sub>	Small Signal current Gain	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}, f = 20 \text{MHz}$	2.5	25		
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = -10V, I_E = 0, f = 1.0MHz$		30	pF	
Pulse Test: Pulse	Width ≤ 300μs, Duty Cycle ≤ 1.0%			•	•	

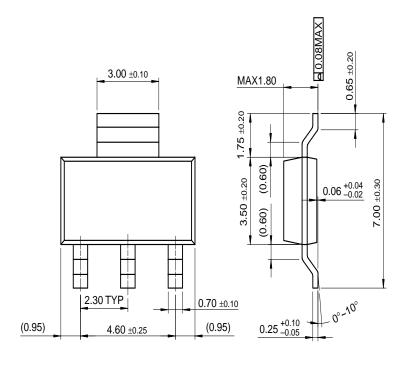
# Thermal Characteristics $T_a=25$ °C unless otherwise noted

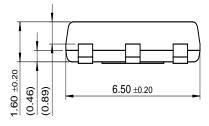
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

<sup>\*</sup> Device mounted on FR-4PCB 36mm × 18mm × 1.5mm; mounting pad for the collector lead min. 6cm<sup>2</sup>.

# **Package Dimensions**

# **SOT-223**





Dimensions in Millimeters

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### **Definition of Terms**

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